

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

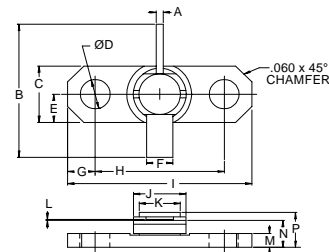
The **ASI MLN1033F** is Designed for Class A Linear Applications up to 1.0 GHz.

FEATURES:

- Class A Operation
- $P_G = 12$ dB at 2.0 W/1.0 GHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	0.5 A
V_{CB0}	40 V
V_{CES}	25 V
V_{EBO}	3.5 V
P_{DISS}	20.6 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	17 °C/W

PACKAGE STYLE .250 2L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.028 / 0.71	.032 / 0.81
B	.740 / 18.80	
C	.245 / 6.22	.255 / 6.48
D	.128 / 3.25	.132 / 3.35
E		.125 / 3.18
F	.110 / 2.79	.117 / 2.97
G		.117 / 2.97
H	.560 / 14.22	.570 / 14.48
I	.790 / 20.07	.810 / 20.57
J	.225 / 5.72	.235 / 5.97
K	.165 / 4.19	.185 / 4.70
L	.003 / 0.08	.007 / 0.18
M	.058 / 1.47	.068 / 1.73
N	.119 / 3.02	.135 / 3.43
P	.149 / 3.78	.187 / 4.75

ORDER CODE: ASI10626
CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	$I_C = 2.0$ mA	40			V
BV_{CEO}	$I_C = 5.0$ mA	25			V
BV_{EBO}	$I_E = 2.0$ mA	3.5			V
h_{FE}	$V_{CE} = 5.0$ V $I_C = 400$ mA	15		150	---
P_G	$V_{CE} = 18$ V $I_{CQ} = 220$ mA $f = 1.0$ GHz $P_{OUT} = 2.0$ W	12			dB